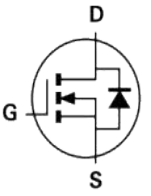
N-Channel Enhancement Mode Power MOSFET

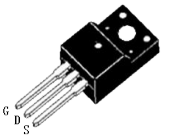
MAIN CHARACTERISTICS

I_D	8A
V_{DSS}	500V
R_{DSON}-typ （@V_{GS}=10V）	0.68Ω

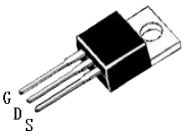


FEATURES

- Fast Switching
- Low ON Resistance
- Low Gate Charge
- 100% Single Pulse avalanche energy Test



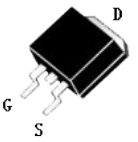
TO-220F



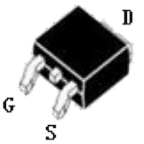
TO-220

APPLICATIONS

- Power switch circuit of adaptor and charger.



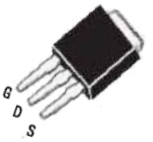
TO-263



TO-252

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275℃ maximum,10s per JESD 22-B106



TO-251

Product specification classification

Part Number	Package	Mark	Pack
FTK8N50P	TO-220	FTK8N50	Tube
FTK8N50F	TO-220F	FTK8N50	Tube
FTK8N50DD	TO-263	FTK8N50	Tape
FTK8N50I	TO-251	FTK8N50	Tube
FTK8N50D	TO-252	FTK8N50	Tube

N-Channel Enhancement Mode Power MOSFET

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value			Unit
		220/263	220F	251/252	
Drain-Source Voltage	V_{DS}	500			V
Gate-Source Voltage	V_{GS}	±30			V
Continue Drain Current	I_D	8			A
Pulsed Drain Current (Note1)	I_{DM}	32			A
Power Dissipation	P_D	100	35	100	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	440			mJ
Operating Temperature Range	T_J	150			°C
Storage Temperature Range	T_{STG}	-55 to +150			°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.25	3.57	1.25	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	62.5	62.5	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS} = 0 V,I_D = 250 μA	BV_{DSS}	500	-	-	V
Drain-Source Leakage Current	V_{DS} = 500 V, V_{GS} = 0 V	I_{DSS}	-	-	1	μA
Gate Leakage Current	V_{GS} = ± 30 V, V_{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V_{DS} = V_{GS} , I_D = 250 μA	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	V_{GS} = 10 V, I_D = 4 A	$R_{DS(on)}$	-	0.68	0.8	Ω
Forward Transconductance	V_{DS} = 15 V, I_D = 4 A	gfs	-	7	-	S
Input Capacitance	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{iss}	-	891	-	pF
Output Capacitance		C_{oss}	-	110	-	pF
Reverse Transfer Capacitance		C_{rss}	-	7	-	pF
Turn-on Delay Time(Note2)	I_D = 8 A, V_{DD} = 250V, R_G= 10 Ω	$t_{d(ON)}$	-	18	-	ns
Rise Time(Note2)		t_r	-	20	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	44	-	ns
Fall Time(Note2)		t_f	-	15	-	ns
Total Gate Charge(Note2)	I_D = 8 A, V_{DD} = 400 V, V_{GS} = 10 V	Q_G	-	22	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	5	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	9	-	nC

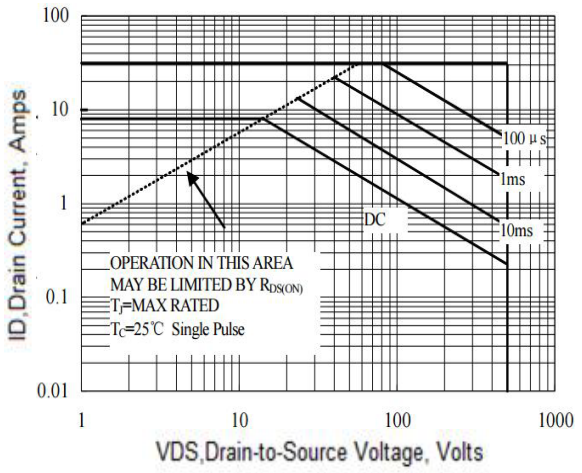
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

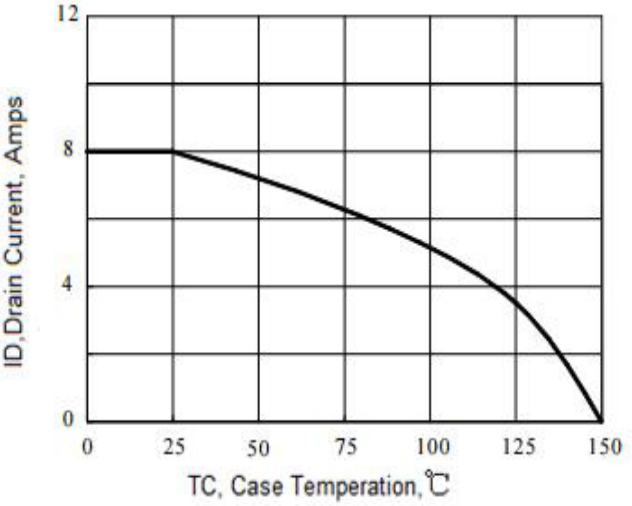
Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current	TC = 25 ° C	I_S	-	-	8	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	32	A
Drain-Source Diode Forward Voltage	I_{SD} = 8 A	V_{SD}	-	-	1.4	V
Reverse Recovery Time(Note2)	IS=8A,Tj = 25℃ dIF/dt=100A/us, VGS=0V	trr	-	340	-	ns
Reverse Recovery Charge(Note2)		Qrr	-	1.7	-	μC

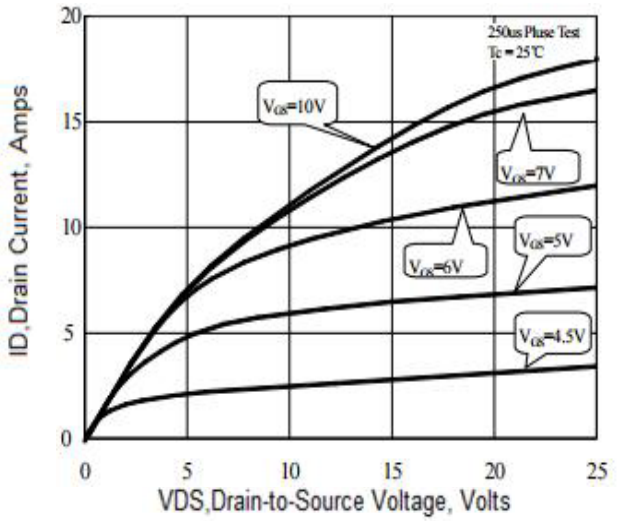
Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

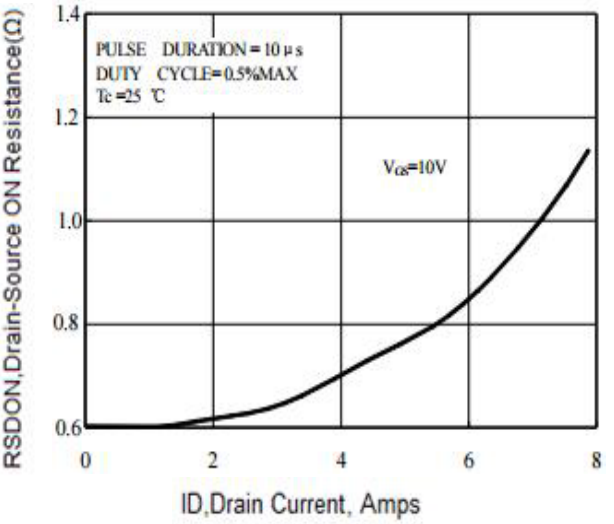
N-Channel Enhancement Mode Power MOSFET

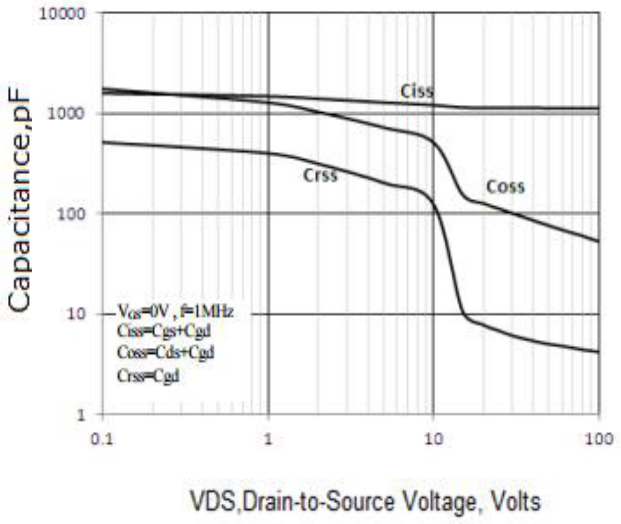
RATINGS AND CHARACTERISTIC CURVES

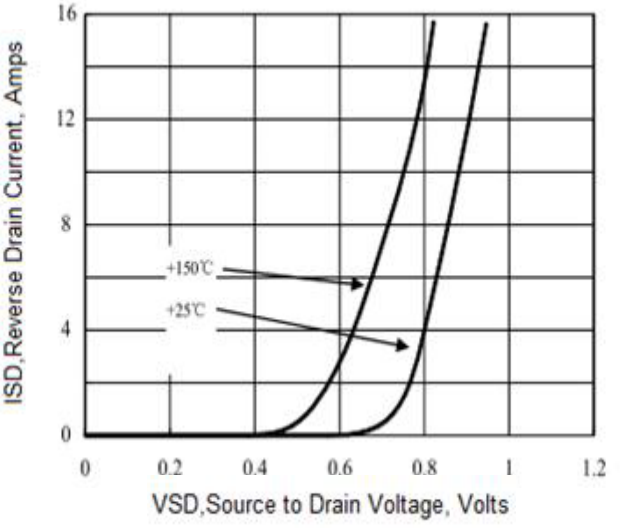








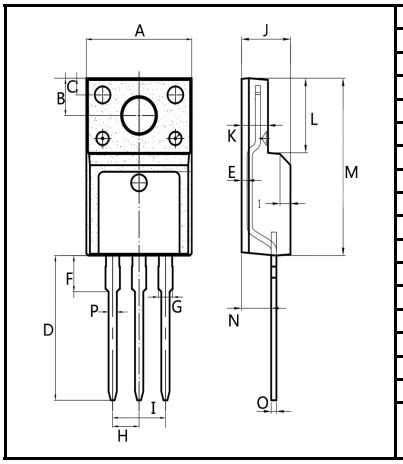




N-Channel Enhancement Mode Power MOSFET

Package Outline Dimensions millimeters

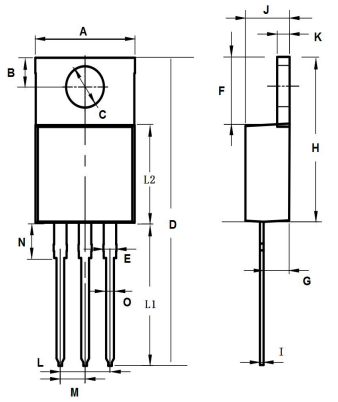
TO-220F



Dim.	Min.	Max.
A	9.95	10.35
B	2.95	3.25
C	1.25	1.45
D	12.65	12.95
E	0.4	0.6
F	2.8	3.5
G	1.3	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.6	4.75
K	2.45	2.65
L	6.45	6.85
M	15.4	16
N	2.75	3.05
O	0.45	0.55
P	0.7	0.9

All Dimensions in millimeter

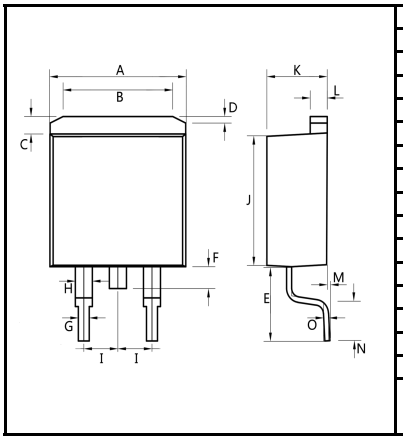
TO-220



Dim.	Min.	Max.
A	10.15	10.35
B	2.5	2.95
C	3.7	3.9
D	28.5	29.5
E	1.2	1.4
F	6.2	6.55
G	2.85	3.25
H	15	16
I	0.35	0.42
J	4.3	4.55
K	1.2	1.4
L	Typ5.08	
L1	13	14
L2	8.5	9.5
M	Typ2.54	
N	2.8	3.5
O	0.7	0.9

All Dimensions in millimeter

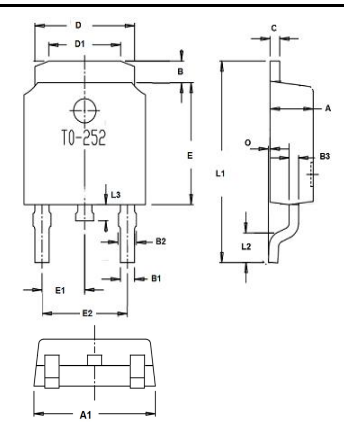
TO-263



Dim.	Min.	Max.
A	10.1	10.35
B	6	8
C	1.2	1.5
D	0.55	1
E	4.3	5.3
F	1.4	1.6
G	0.75	0.85
H	1.2	1.5
I	Typ2.54	
J	8.5	9.5
K	4.3	4.55
L	1.25	1.35
M	0.02	0.23
N	2.2	2.8
O	0.3	0.4

All Dimensions in millimeter

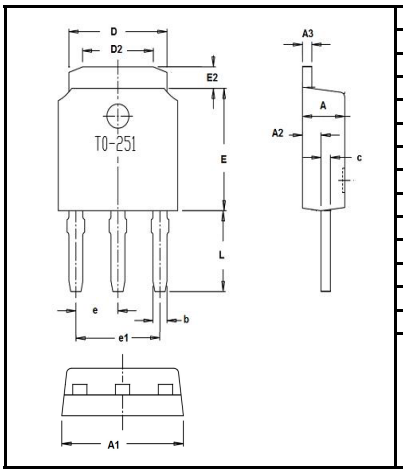
TO-252



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.95	1.55
B1	0.6	0.8
B2	0.75	0.95
C	Typ0.5	
D	5.3	5.5
D1	3.65	4.05
E	5.8	6.4
E1	Typ2.3	
E2	Typ4.6	
O	0	0.15
L1	9	11
L2	Typ1.5	
L3	0.7	1

All Dimensions in millimeter

TO-251



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
A2	0.9	1.1
A3	Typ0.5	
b	0.6	0.8
c	0.4	0.5
D	5.3	5.5
D2	3.65	4.05
E	5.8	6.4
E2	0.9	1.4
e	Typ2.29	
e1	Typ4.58	
L	3.7	4.3

All Dimensions in millimeter